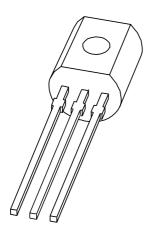
DISCRETE SEMICONDUCTORS

DATA SHEET



BF199NPN medium frequency transistor

Product data sheet Supersedes data of 1997 Jul 07 2004 Nov 08



NPN medium frequency transistor

BF199

FEATURES

- Low current (max. 25 mA)
- Low voltage (max. 25 V).

APPLICATIONS

• Output stage of a vision IF amplifier.

DESCRIPTION

NPN medium frequency transistor in a TO-92; SOT54 plastic package.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

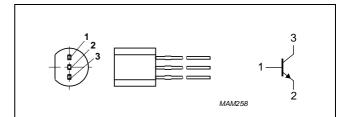


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	_	40	V
V_{CEO}	collector-emitter voltage	open base	_	-	25	V
I _{CM}	peak collector current		_	-	25	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	_	500	mW
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 7 mA	38	_	_	
f _T	transition frequency	V _{CE} = 10 V; I _C = 5 mA; f = 100 MHz	_	550	_	MHz

ORDERING INFORMATION

TYPE NUMBER			
TIPE NUMBER	NAME	DESCRIPTION	VERSION
BF199	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

NPN medium frequency transistor

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	_	25	V
V _{EBO}	emitter-base voltage	open collector	_	4	V
I _C	collector current (DC)		_	25	mA
I _{CM}	peak collector current		-	25	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 40 V; I _E = 0 A	_	_	100	nA
I _{EBO}	emitter-base cut-off current $V_{EB} = 4 \text{ V}; I_{C} = 0 \text{ A}$		_	_	100	nA
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 7 \text{ mA}$	38	_	_	
V_{BE}	base-emitter voltage	$V_{CE} = 10 \text{ V}; I_{C} = 7 \text{ mA}$	_	775	925	mV
C_{re}	feedback capacitance	$V_{CB} = 10 \text{ V}; I_C = 0 \text{ A}; f = 1 \text{ MHz}$	_	_	0.5	pF
f_{T}	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 5 \text{ mA}; f = 100 \text{ MHz}$	_	550	_	MHz

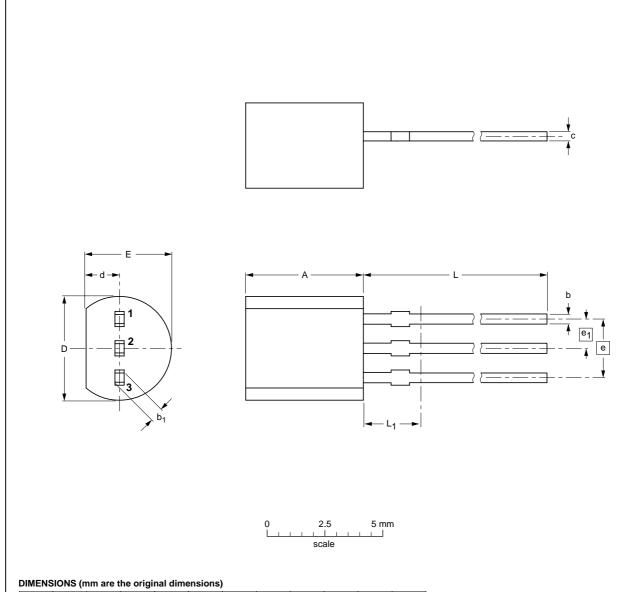
NPN medium frequency transistor

BF199

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	EUROPEAN ISSUE DATI			
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43A		-04-06-28- 04-11-16	

NPN medium frequency transistor

BF199

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

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